Description

This -60V -50A P-Channel MOSFET in a TO-220 Plastic Package.

Applications

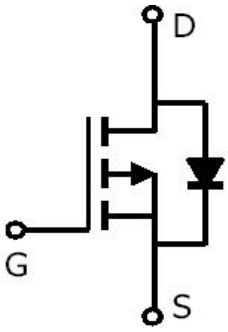
Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products

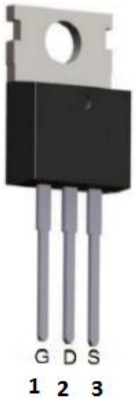
Features

- Low RDS(on)
- Low gate charge
- Low Crss
- Fast switching

V_{DSS}	$R_{DS(on)}$(Typ)	I_D
-60V	30mΩ	-50A

Equivalent Circuit & Pinning





Absolute Maximum Ratings(Ta=25℃)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	-60	V
Drain Current		I_D(Tc=25℃)	-50	A
Drain Current - Pulsed		I_{DM}	-200	A
Gate-Source Voltage		V_{GS}	±20	V
Power Dissipation		P_D(Tc=25℃)	118	W
Single Pulsed Avalanche Energy		E_{AS}	250	mJ
Avalanche Current(L=0.5mH)		I_{AS}	25	A
Junction and Storage Temperature Range		T_j, T_{stg}	-55 to 150	℃
Thermal resistance, junction - ambient	t ≤ 10s	$R_{\theta JA}$	15	℃/ W
	Steady-State		60	
Thermal resistance, junction - case	Steady-State	$R_{\theta JC}$	1.1	

Electrical Characteristics(Ta=25℃)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-60	-68		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-60V V_{GS}=0V			-1.0	μA
		V_{DS}=-48V T_C=150℃			-10	
Gate-Body Leakage Current Forward	I_{GSS}	V_{GS}=±20V V_{DS}=0V			±0.1	μA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=-250μA	-1	-1.6	-3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=-10V I_D=-20A		30	35	mΩ
	$R_{DS(on)}$	V_{GS}=-4.5V I_D=-10A		40	45	mΩ
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V I_S=-1A			-1.2	V
Gate resistance	Rg			10		Ω
Input Capacitance	C_{iss}	V_{DS}=-25V V_{GS}=0V f=1.0MHz		3200		pF
Output Capacitance	C_{oss}			800		pF
Reverse Transfer Capacitance	C_{rss}			270		pF
Total Gate Charge	$Q_{g(10V)}$	V_{GS}=-10V, V_{DS}=-30V, I_D=-20A		45		nC
Total Gate Charge	$Q_{g(4.5V)}$			23		
Gate Source Charge	Q_{gs}			9.3		
Gate Drain Charge	Q_{gd}			10.2		nC
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=-10V V_{DS}=-30V R_L=1.5 R_{GEN}=3Ω		12		ns
Turn-On Rise Time	t_r			14.5		
Turn-Off Delay Time	$t_{d(off)}$			38		
Turn-Off Fall Time	t_f			15		

Electrical Characteristic Curve

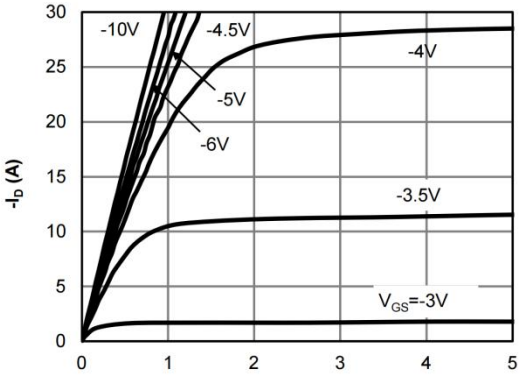


Figure 1: On-Region Characteristics

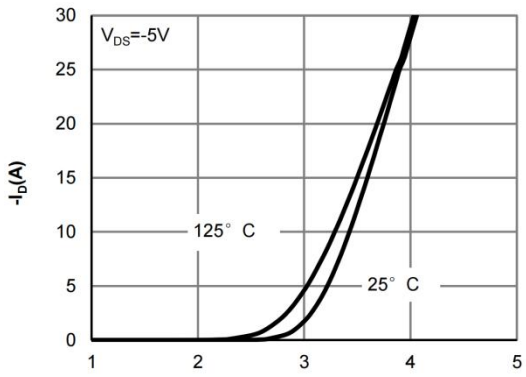


Figure 2: Transfer Characteristics

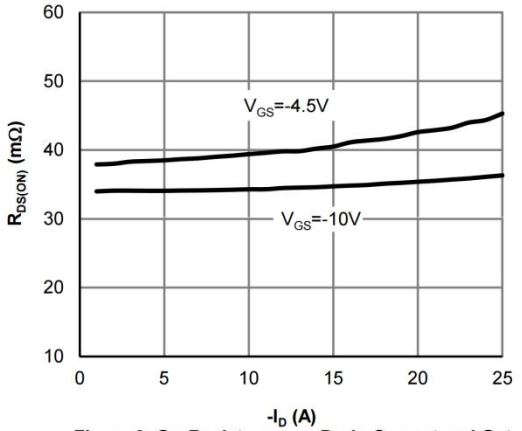


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

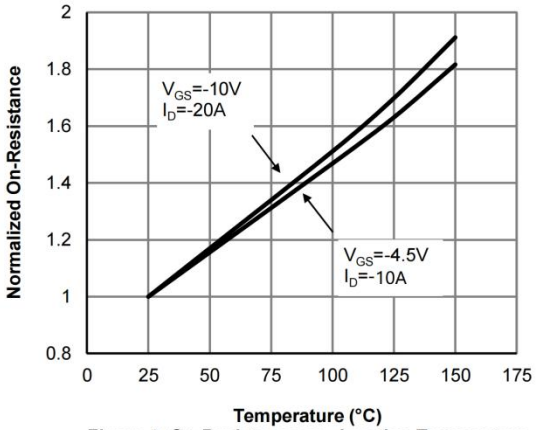


Figure 4: On-Resistance vs. Junction Temperature

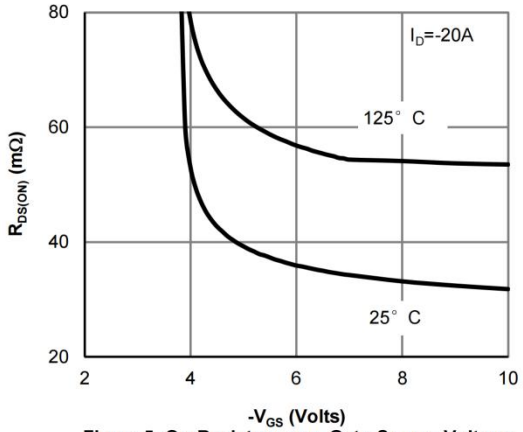


Figure 5: On-Resistance vs. Gate-Source Voltage

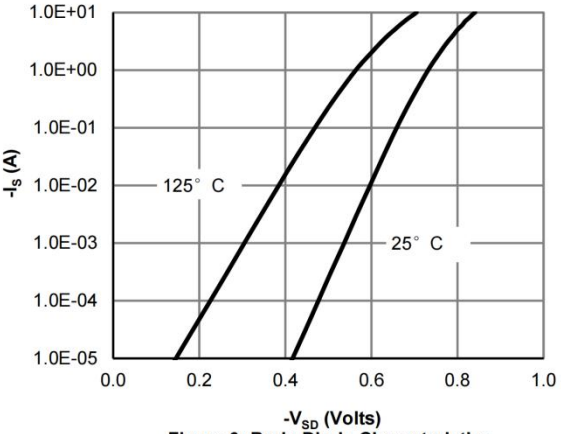


Figure 6: Body-Diode Characteristics

Electrical Characteristic Curve

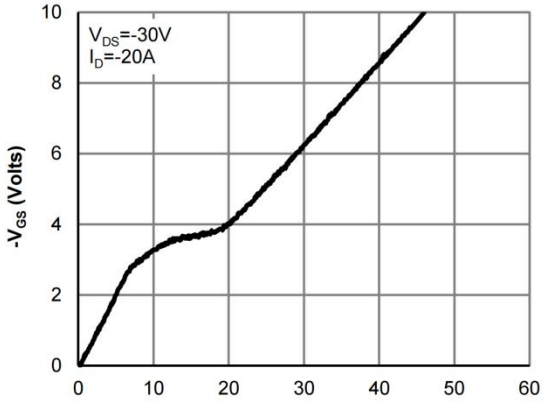


Figure 7: Gate-Charge Characteristics

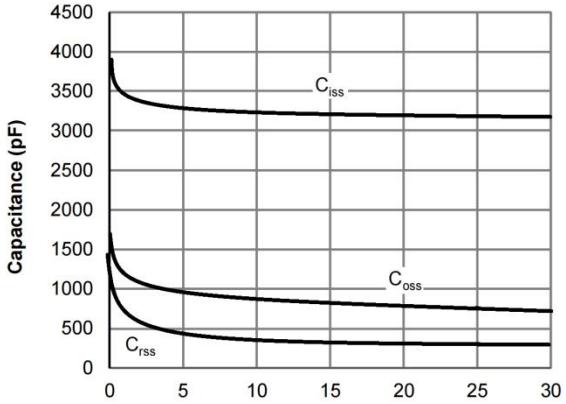
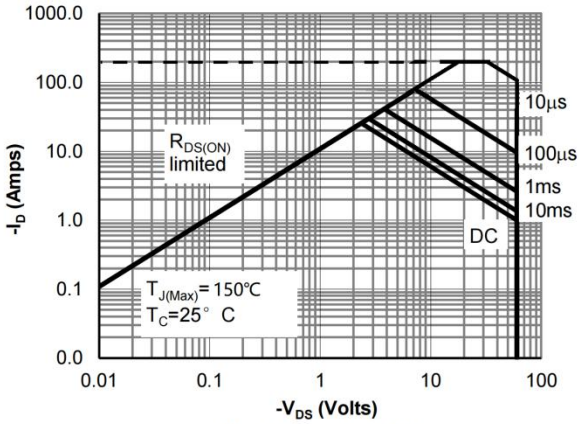


Figure 8: Capacitance Characteristics



V_{GS}> or equal to 4.5V
Figure 9: Maximum Forward Biased Safe Operating Area

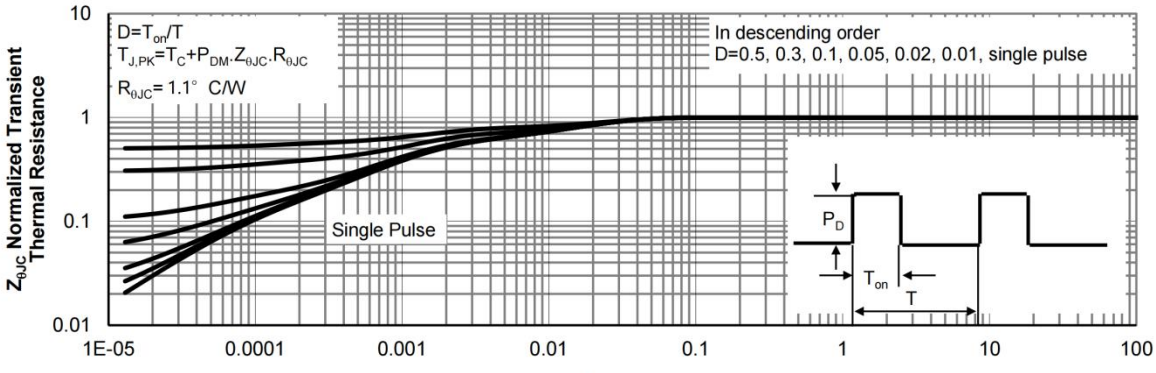
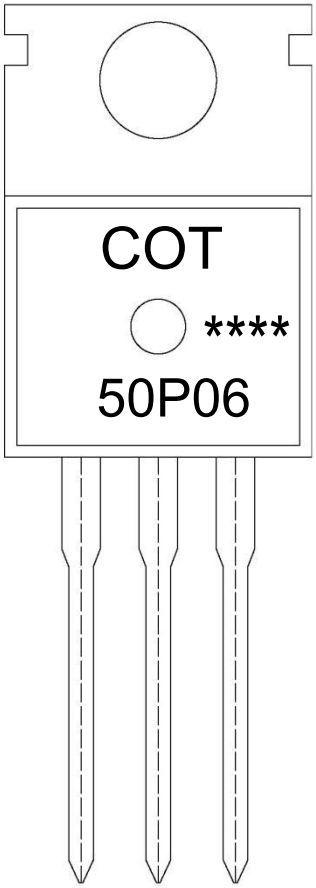


Figure 10: Normalized Maximum Transient Thermal Impedance

Marking Instructions



Note:

COT: Company Logo.

50P06: Product Type.

****: Lot No. Code, code change with Lot No.

Packaging SPEC.

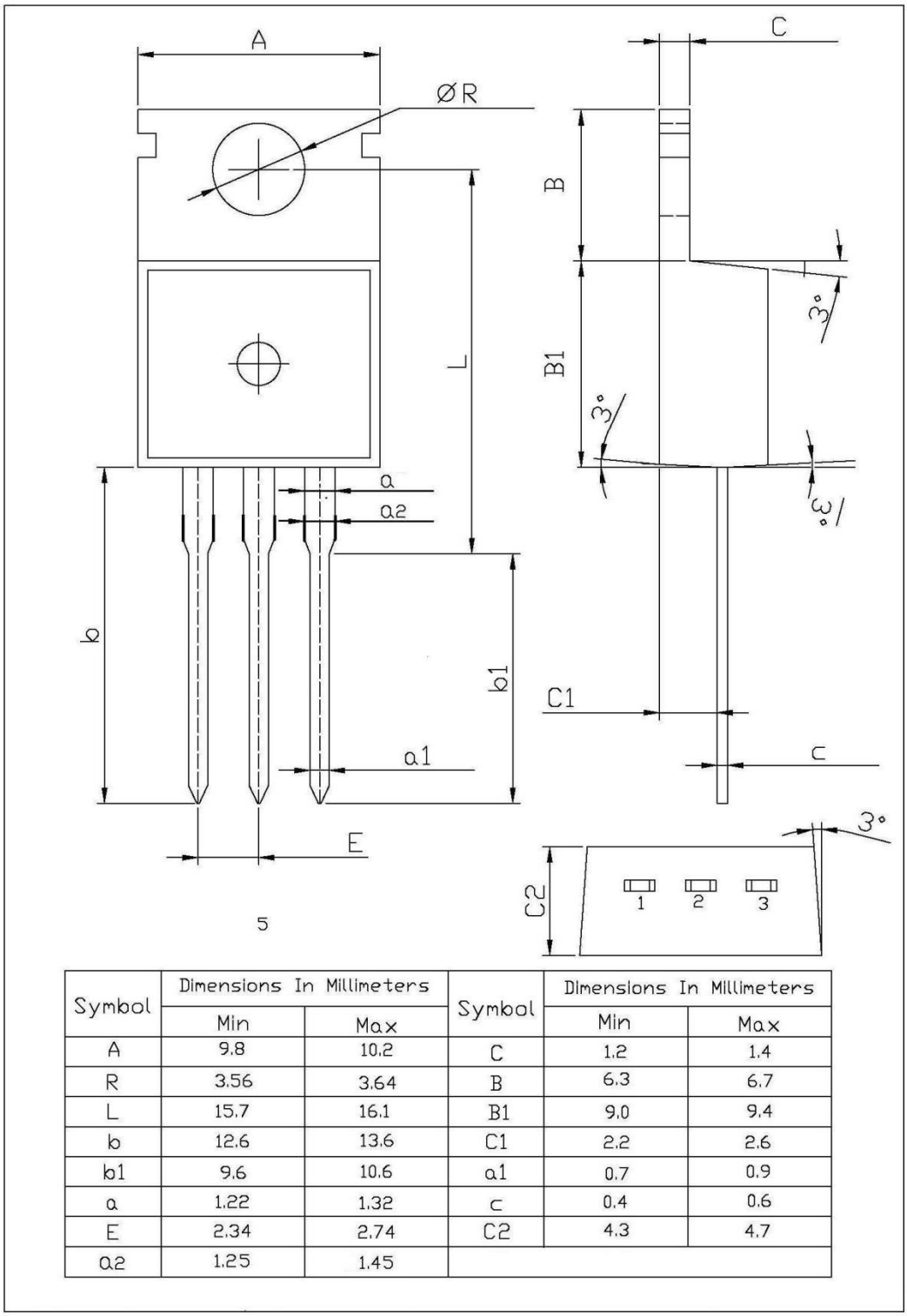
BULK AND TUBE INFOMATIONS

Package Type	Units					Dimension (unit: mm³)		
	Units/Bag	Bags/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Bag	Inner Box	Outer Box
TO-220/F	200	10	2,000	5	10,000	135×190	237×172×102	560×245×195

Package Type	Units					Dimension (unit: mm³)		
	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Tube	Inner Box	Outer Box
TO-220/F	50	20	1,000	5	5,000	532×31.4×5.5	555×164×50	575×290×180

Package Outline Dimensions

TO-220 单位：mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	9.8	10.2	C	1.2	1.4
R	3.56	3.64	B	6.3	6.7
L	15.7	16.1	B1	9.0	9.4
b	12.6	13.6	C1	2.2	2.6
b1	9.6	10.6	a1	0.7	0.9
a	1.22	1.32	c	0.4	0.6
E	2.34	2.74	C2	4.3	4.7
a2	1.25	1.45			